



65-2604

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Express Mail No.: EV 346 811 025US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Cécile AULNETTE et al.

Confirmation No.: 7888

Application No: 10/763,978

Group Art Unit: 2811

Filing Date: January 22, 2004

Examiner:

For: SEMICONDUCTOR STRUCTURE FOR  
PROVIDING STRAINED CRYSTALLINE LAYER ON  
INSULATOR AND METHOD FOR FABRICATING  
SAME

Atty. Docket No.: 4717-7300

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, applicants submit herewith five ( 5 ) references for the Examiner's review and consideration. These references were brought to the attention of the applicants and were cited in the European Search Report and a copy is enclosed.

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee is believed to be due for the filing of this statement as it is being submitted prior to an initial office action for this application. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

Respectfully submitted,

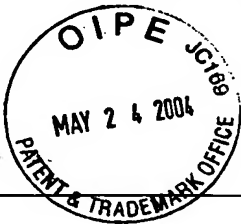
Date: \_\_\_\_\_

5/24/04

Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP  
CUSTOMER NO. 28765  
(212) 294-3311

Enclosures

|   |    |  |                |   |              |                                       |                               |
|---|----|--|----------------|---|--------------|---------------------------------------|-------------------------------|
| <b>LIST OF REFERENCES CITED BY APPLICANT</b><br><i>(Use several sheets if necessary)</i>  |    |  |                | ATTY. DOCKET NO.:<br><b>4717-7300</b>       |              | APPLICATION NO.:<br><b>10/763,978</b> |                               |
|   |    |  |                | APPLICANT:<br><b>Cecile AULNETTE et al.</b> |              |                                       |                               |
|   |    |  |                | FILING DATE:<br><b>January 22, 2004</b>     |              | GROUP:<br><b>2811</b>                 |                               |
| <b>U.S. PATENT DOCUMENTS</b>  |    |  |                |   |              |                                       |                               |
| *EXAMINER<br>INITIAL  | AA | DOCUMENT NUMBER<br>6,039,803   | DATE<br>3/2000 | NAME<br>Fitzgerald et al.                   | CLASS<br>117 | SUBCLASS<br>89                        | FILING DATE IF<br>APPROPRIATE |
|   | AB | 2002/0084000 A1  | 7/2002         | Fitzgerald                                  | 148          | 33.2                                  |                               |
|   | AC |  |                |   |              |                                       |                               |
| <b>FOREIGN PATENT DOCUMENTS</b>   |    |  |                |   |              |                                       |                               |
|   |    | DOCUMENT NUMBER  | DATE           | COUNTRY                                     | CLASS        | SUBCLASS                              | TRANSLATION<br>YES NO         |
|   | AD |  |                |   |              |                                       |                               |
|   | AE |  |                |   |              |                                       |                               |
| <b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>  |    |  |                |   |              |                                       |                               |
|   | AF | B. Gallas et al., <b>"Influence of misfit and threading dislocations on the surface morphology of SiGe graded-layers"</b> ,; Journal of Crystal Growth 201/202, pp 547-550, (1999)   |                |   |              |                                       |                               |
|   | AG | Douglas Paul, <b>"The Physics, Material and Devices of Silicon Germanium Technology"</b> , Physics World, pp. 1-14.  |                |   |              |                                       |                               |
|   | AH | Asano et al., <b>"Structural characterization of Si<sub>1</sub>-Ge<sub>x</sub> alloy layers grown by molecular beam epitaxy on Si(001) substrates"</b> , American Institute of Physics, Journal of Applied Physics, Vol. 87, No. 12, pp 8759-8765 (2000) |                |   |              |                                       |                               |
|   | AI |  |                |   |              |                                       |                               |
|   | AJ |  |                |   |              |                                       |                               |
|   |    |  |                |   |              |                                       |                               |
| <b>EXAMINER</b>   |    |  |                | <b>DATE CONSIDERED</b>                      |              |                                       |                               |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |    |  |                |   |              |                                       |                               |



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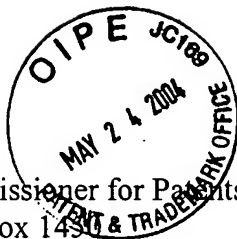
The following items listed below are being filed herewith with the USPTO on May 24, 2004

| Express Mail No. <b>EV 346 811 025 US</b> |                                  |   |
|---|----------------------------------|---|
| Attorney Docket<br>No.                    | Appln. Serial No./<br>Patent No. | Items - Documents filed on <b>May 24, 2004</b>  |
| 4717-7300                                 | <b>10/763,978</b>                | Supplemental Information Disclosure Statement, Form PTO 1449,<br>5 refs.; Submission of Certified Copy of Priority; Document No.<br>EP 03290231.4 |

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The following items listed below are being filed herewith with the USPTO on May 24, 2004

| Express Mail No. <b>EV 346 811 025 US</b> |                               |  |
|---|-------------------------------|--|
| Attorney Docket No.                       | Appln. Serial No./ Patent No. | Items - Documents filed on May 24, 2004  |
| 88265-349                                 | <b>09/640,772</b>             | Amendment (9 pages)  |
| 88265-7079                                | <b>09/935,064</b>             | Petition for Extension of Time (in duplicate); Amendment   |
| 4717-7300                                 | <b>10/763,978</b>             | Supplemental Information Disclosure Statement, Form PTO 1449, 5 refs.; Submission of Certified Copy of Priority; Document No. EP 03290231.4  |
| 85189-6200                                | <b>TBA</b>                    | Utility Patent Application Transmittal (PTO/SB/05); Specification 60 pages including 31 claims; Formal Drawings for Figs. 1-15 (19 sheets); Patent Application Fee Sheet (in duplicate); Executed Inventors' Declaration; Sequence Listing in paper form (12 sheets) |

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